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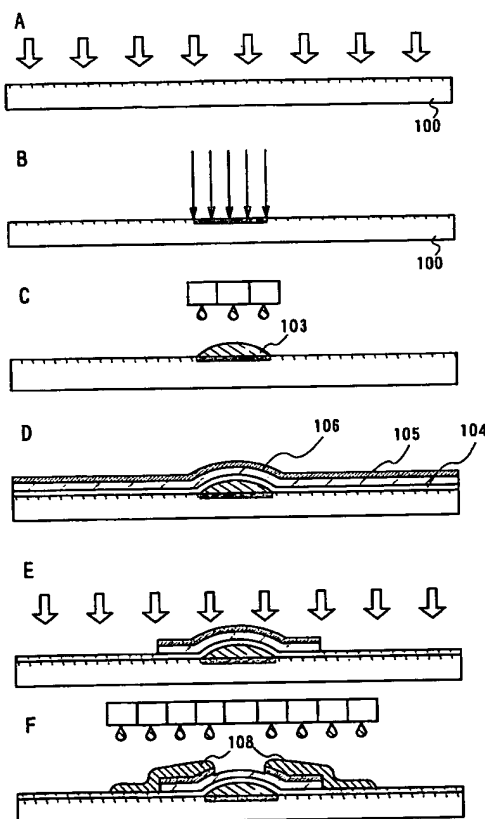
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(54) Title: METHOD FOR FORMING WIRING, METHOD FOR MANUFACTURING THIN FILM TRANSISTOR AND  
DROPLET DISCHARGING METHOD



(57) Abstract: It is required that a line width of a wiring is prevented from being wider to be miniaturized when the wiring or the like is formed by a dropping method typified by an ink-jetting method. Therefore, the invention provides a method for narrowing (miniaturizing) the line width according to a method different from a conventional method. A region to be liquid-repellent is formed and further, a region to be lyophilic is formed selectively in the region to be liquid-repellent in a surface for forming a pattern, before forming a desired pattern. After that, a pattern for a wiring or the like is formed in the lyophilic region by a dropping method typified by an ink-jetting method for dropping a composition including a conductive material for the wiring or the like.



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